IXYS

HiPerFET™ Power MOSFETs Q-Class

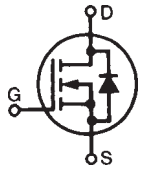
IXFH 30N60Q
IXFT 30N60Q

V_{DSS} = 600 V
I_{D25} = 30 A
$R_{DS(on)}$ = 0.23 Ω

$t_{rr} \leq 250$ ns

N-Channel Enhancement Mode
Avalanche Rated, High dv/dt, Low Q_g

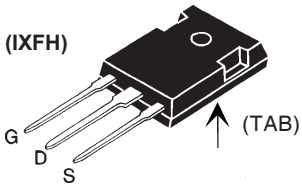
Preliminary Data Sheet



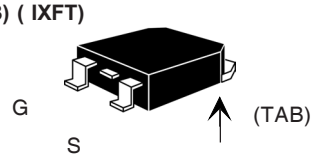
Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C	600	V
V_{DGR}	T_J = 25°C to 150°C; R_{GS} = 1 MΩ	600	V
V_{GS}	Continuous	±20	V
V_{GSM}	Transient	±30	V
I_{D25}	T_C = 25°C	30	A
I_{DM}	T_C = 25°C, pulse width limited by T_{JM}	120	A
I_{AR}	T_C = 25°C	30	A
E_{AR}	T_C = 25°C	45	mJ
E_{AS}	T_C = 25°C	1.5	J
dv/dt	$I_S \leq I_{DM}$, di/dt ≤ 100 A/µs, $V_{DD} \leq V_{DSS}$, $T_J \leq 150°C$, R_G = 2 Ω	10	V/ns
P_D	T_C = 25°C	500	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_L	1.6 mm (0.063 in) from case for 10 s	300	°C
M_d	Mounting torque TO-247	1.13/10	Nm/lb.in.
Weight	TO-247	6	g
	TO-268	4	g

Symbol	Test Conditions (T_J = 25°C, unless otherwise specified)	Characteristic Values min.	typ.	max.	
V_{DSS}	V_{GS} = 0 V, I_D = 250µA	600			V
	Temperature Coefficient		0.095		%/K
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 4 mA	2.5		4.5	V
	Temperature Coefficient		- 0.24		%/K
I_{GSS}	V_{GS} = ±20 V_{DC}, V_{DS} = 0			±200	nA
I_{DSS}	$V_{DS} = V_{DSS}$ T_J = 25°C			25	µA
	V_{GS} = 0 V T_J = 125°C			1	mA
$R_{DS(on)}$	V_{GS} = 10 V, $I_D = 0.5 \bullet I_{D25}$ Pulse test, t ≤ 300 µs, duty cycle d ≤ 2 %			0.23	Ω

TO-247 AD (IXFH)



TO-268 (D3) (IXFT)



G = Gate D = Drain
S = Source TAB = Drain

Features

- Low gate charge
- International standard packages
- Epoxy meet UL 94 V-0, flammability classification
- Low $R_{DS\ (on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Avalanche energy and current rated
- Fast intrinsic Rectifier

Advantages

- Easy to mount
- Space savings
- High power density

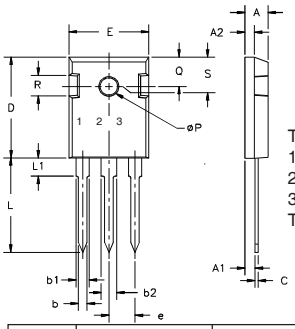
© 2003 IXYS All rights reserved

Symbol	Test Conditions	Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
g_{fs}	V_{DS} = 10 V; I_D = 0.5 • I_{D25}, pulse test	14	22		S
C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz		4700		pF
C_{oss}			580		pF
C_{rss}			230		pF
$t_{d(on)}$	V_{GS} = 10 V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25} R_G = 2.0 Ω (External),		30		ns
t_r			32		ns
$t_{d(off)}$			80		ns
t_f			16		ns
$Q_{g(on)}$	V_{GS} = 10 V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		125		nC
Q_{gs}			28		nC
Q_{gd}			76		nC
R_{thJC}				0.25	K/W
R_{thCK}	TO-247		0.25		K/W

Source-Drain Diode

Symbol	Test Conditions	Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
I_S	V_{GS} = 0 V			26	A
I_{SM}	Repetitive; pulse width limited by T_{JM}			104	A
V_{SD}	$I_F = I_S$, V_{GS} = 0 V, Pulse test, t ≤ 300 µs, duty cycle d ≤ 2 %			1.5	V
t_{rr}	$I_F = I_S$ -di/dt = 100 A/µs, V_R = 100 V			250	ns
Q_{RM}			1		µC
I_{RM}			10		A

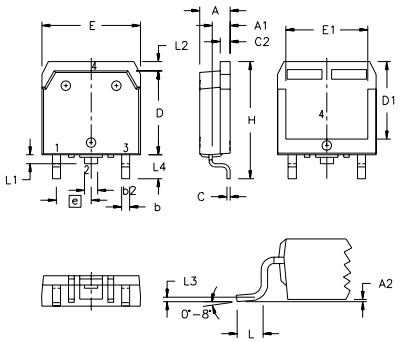
TO-247 AD (IXFH) Outline



Terminals:
1 - Gate
2 - Drain
3 - Source
Tab - Drain

Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.7	5.3	.185	.209
A_1	2.2	2.54	.087	.102
A_2	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b_1	1.65	2.13	.065	.084
b_2	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	242	BSC

TO-268 Outline



Terminals:
1 - Gate
2 - Drain
3 - Source
Tab - Drain

SYM	INCHES MIN	MAX	MILLIMETERS MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:
4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715 6,306,728B1 6,259,123B1 6,306,728B1
4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025 6,404,065B1 6,162,665 6,534,343

Fig. 1. Output Characteristics @ 25 Deg. C

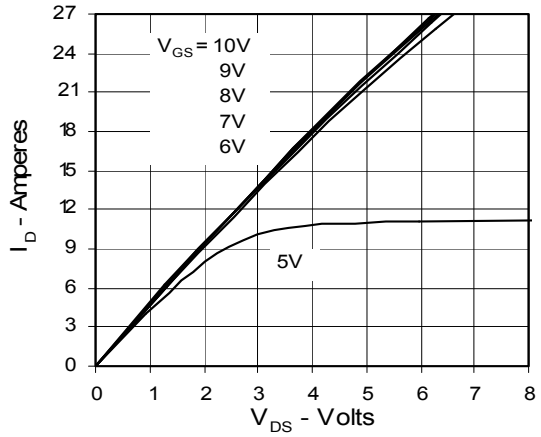


Fig. 2. Extended Output Characteristics @ 25 deg. C

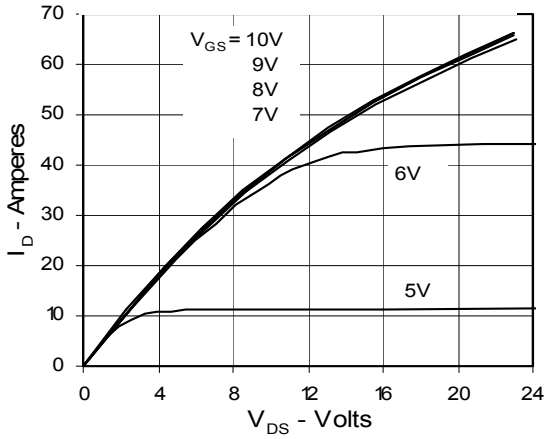


Fig. 3. Output Characteristics @ 125 Deg. C

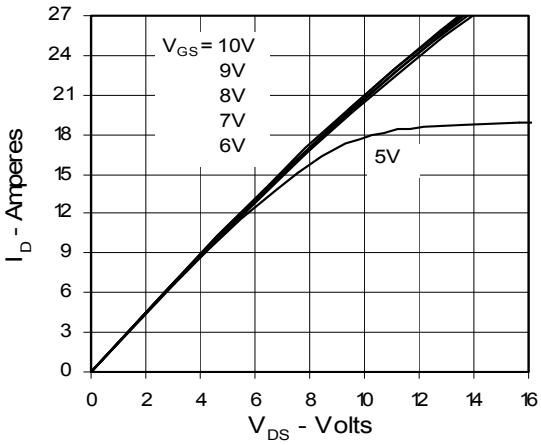


Fig. 4. $R_{DS(on)}$ Normalized to I_{D25} Value vs. Junction Temperature

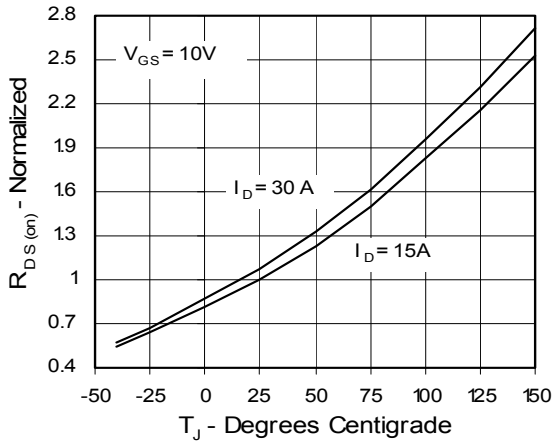


Fig. 5. $R_{DS(on)}$ Normalized to I_{D25} Value vs. I_D

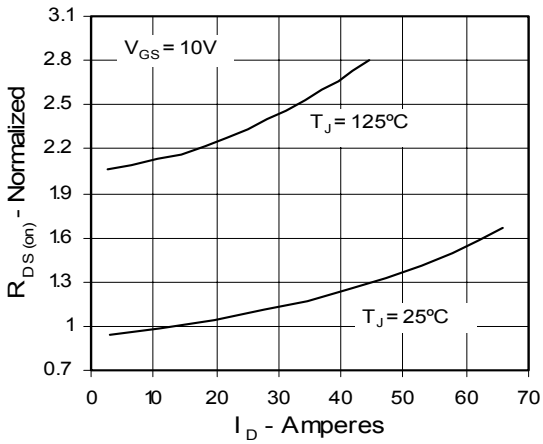
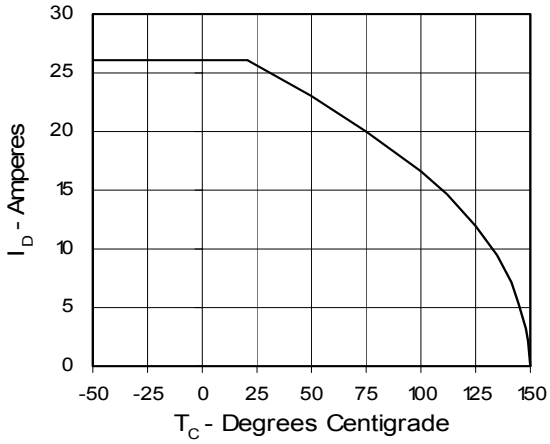


Fig. 6. Drain Current vs. Case Temperature



© 2003 IXYS All rights reserved

Fig. 7. Input Admittance

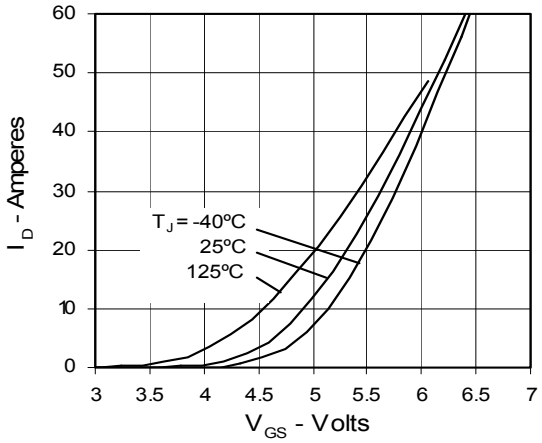


Fig. 8. Transconductance

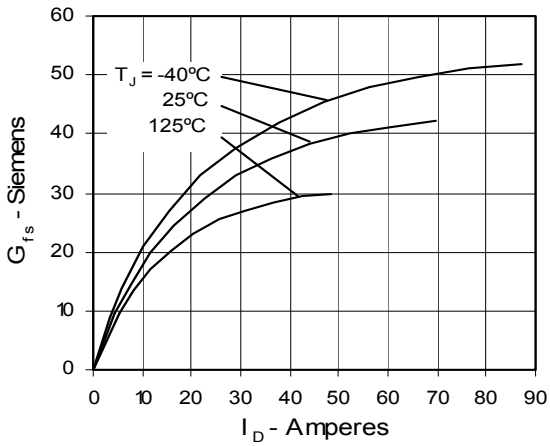


Fig. 9. Source Current vs. Source-To-Drain Voltage

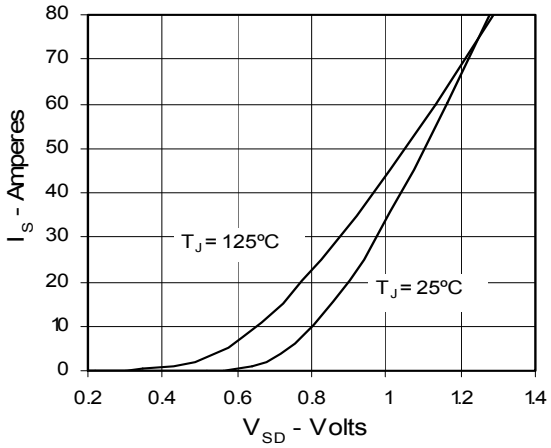


Fig. 10. Gate Charge

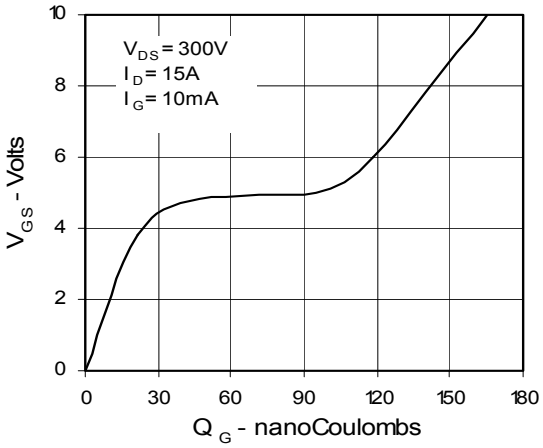


Fig. 11. Capacitance

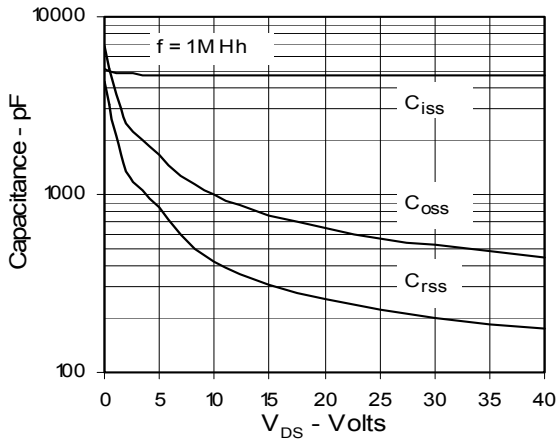
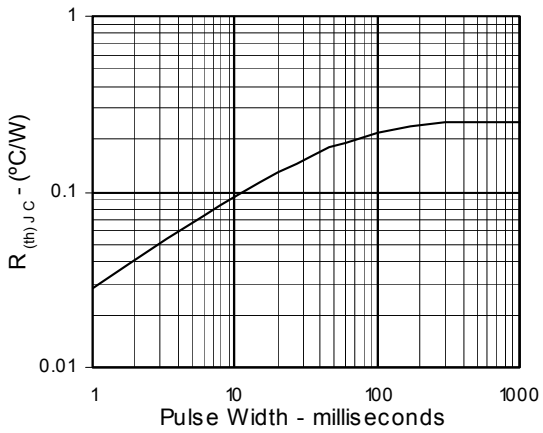


Fig. 12. Maximum Transient Thermal Resistance



IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715 6,306,728B1 6,259,123B1 6,306,728B1 4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025 6,404,065B1 6,162,665 6,534,343